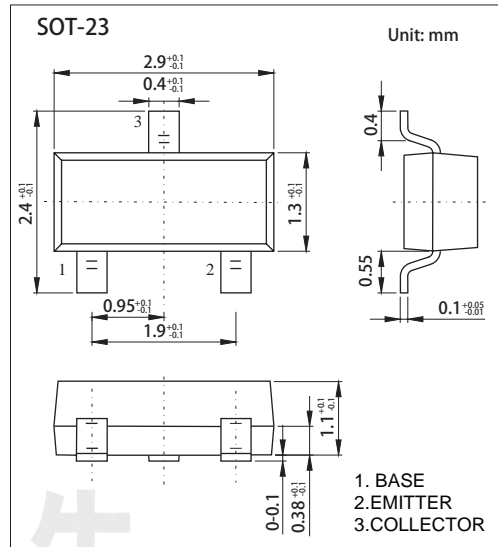


PNP Transistors MMBTA92

■ Features

- High voltage transistor
- Complementary to MMBTA42



■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CB0}	-300	V
Collector - Emitter Voltage	V_{CE0}	-300	
Emitter - Base Voltage	V_{EB0}	-5	
Collector Current - Continuous	I_C	-200	mA
Collector Current - Pulsed	I_{CM}	-500	
Collector Power Dissipation	P_C	300	mW
Thermal Resistance From Junction To Ambient	$R_{\theta JA}$	417	$^\circ\text{C}/\text{W}$
Junction Temperature	T_J	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to 150	

Transistor

PNP Transistors MMBTA92

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditons	Min	Typ	Max	Unit
Collecto- base breakdown voltage	V _{CB0}	I _c = -100 μA, I _E =0	-300			V
Collector- emitter breakdown voltage	V _{CEO}	I _c = -1 mA, I _B =0	-300			
Emitter - base breakdown voltage	V _{EB0}	I _E = -100 μA, I _C =0	-5			
Collector cut-off current	I _{CB0}	V _{CB} = -200 V, I _E =0			-0.25	μA
Emitter cut-off current	I _{EB0}	V _{EB} = -5V, I _C =0			-0.1	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-20 mA, I _B = -2mA			-0.2	V
Base - emitter saturation voltage	V _{BE(sat)}	I _C =-20 mA, I _B = -2mA			-0.9	
DC current gain	h _{FE(1)}	V _{CE} = -10V, I _C = -1mA	60			
	h _{FE(2)}	V _{CE} = -10V, I _C = -10mA	100		200	
	h _{FE(3)}	V _{CE} = -10V, I _C = -30mA	60			
Transition frequency	f _T	V _{CE} = -20V I _C = -10mA, f=30MHz	50			MHz

■ Marking

Marking	2D
---------	----

PNP Transistors MMBTA92

Typical Characteristics

